NSN 5961-01-029-7519

Thyristor Semiconductor Device - Page 1 of 2

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Inclosure Material:

Metal

Overall Length:

1.125 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

Between 1.031 inches and 1.062 inches

Thread Size:

0.500 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

75.0 repetitive peak reverse voltage, peak total value and 35.0 reverse voltage, total rms and 50.0 reverse voltage, peak

Current Rating Per Characteristic:

20.00 milliamperes source cutoff current preset

Power Rating Per Characteristic:

5.0 watts small-signal input power, common-collector blank

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius ambient air

Special Features:

Internal junction configuration arrangement pnpn

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 threaded stud and 2 uninsulated wire lead w/terminal lug

Specification Data:

81349-mil-s-19500/204 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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